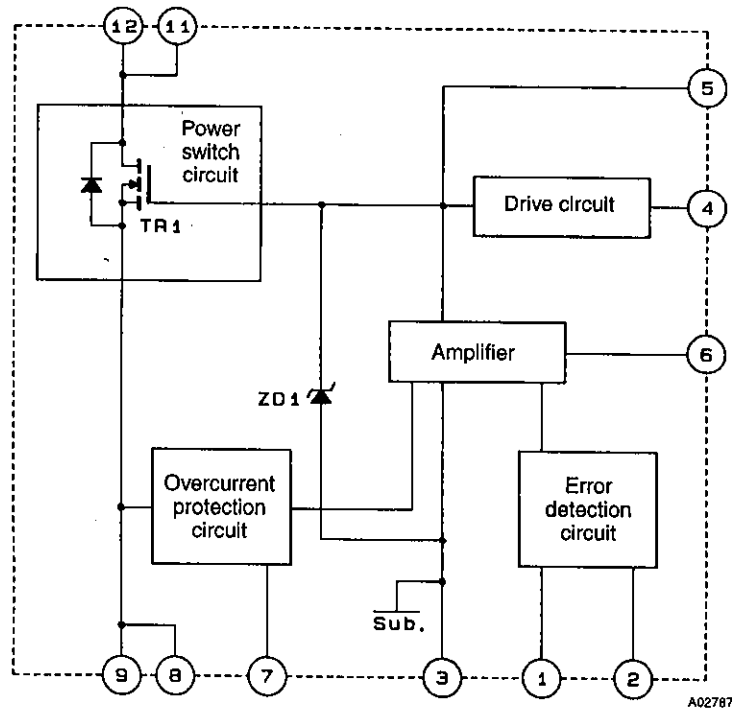


Block Diagram



The back surface of the IC is not an insulator, and is effectively at pin 3 potential.

Pin Functions

Number	Function
1	V_{rel} (40.5V typ) input
2	Error detection level
3	Ground
4	Drive voltage input
5	TR1 gate
6	Amplifier circuit control
7	OCP setting level input
8	TR1 source
9	
11	TR1 drain
12	

Specifications

Maximum Ratings at $T_a = 25^\circ\text{C}$, $T_c = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Operating substrate temperature	$T_c \text{ max}$	Recommended value is 105°C .	115	$^\circ\text{C}$
AC input voltage	V_{AC}	Specified test circuit	280	Vrms
Operating temperature	T_{opg}		-10 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}		-30 to +115	$^\circ\text{C}$
Maximum output power	$W_o \text{ max}$	Specified test circuit, $V_0 = 135\text{V}$	110	W

STK730-060

Parameter	Symbol	Conditions	Ratings	Unit
[TR1]				
Drain current	I_D	Refer to ASO characteristics for overcurrent condition.	3	A
Pulse drain current	$I_{D(pulse)}$		7	A
Drain reverse current	I_{DR}		3	A
Gate-source voltage	V_{GSS}		± 30	V
Allowable power dissipation	P_D		78.1	W
Chip junction temperature	$T_j \text{ max}$		150	$^{\circ}\text{C}$
Thermal resistance	θ_{j-c}		1.6	$^{\circ}\text{C/W}$
[ZD1]				
Allowable power dissipation	P_{ZD1}		500	mW
Chip junction temperature	$T_j(\text{ZD1}) \text{ max}$		125	$^{\circ}\text{C}$
Thermal resistance	$\theta_{j-c}(\text{ZD1})$		0.2	$^{\circ}\text{C/mW}$

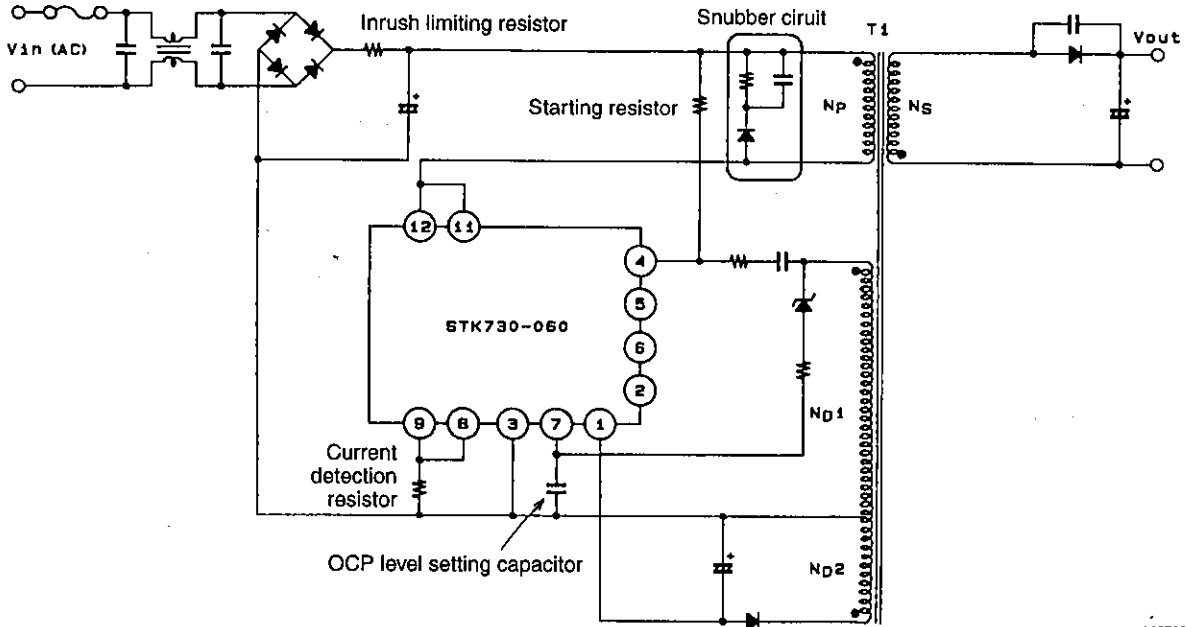
Allowable Operating Ranges at $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Pin 4 input voltage	V_4		± 8 to ± 24	V
Oscillator frequency	f_{osc}		20 to 120	kHz

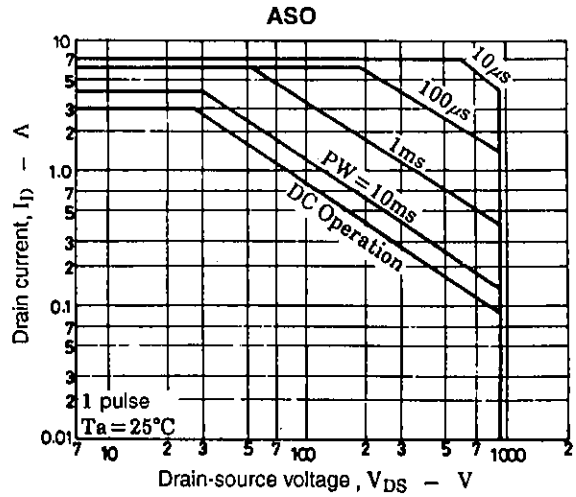
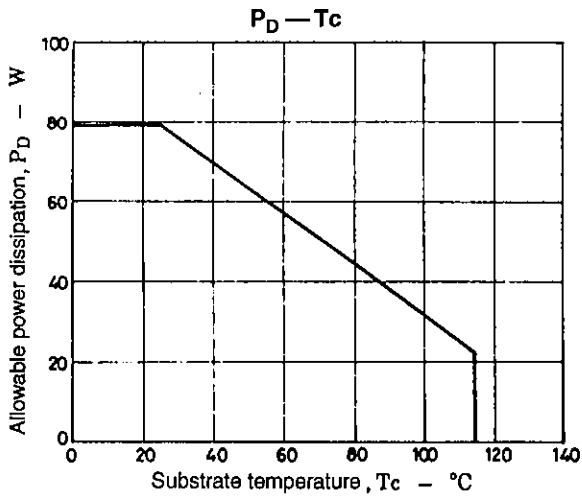
Operating Characteristics at $T_a = 25^{\circ}\text{C}$, $T_c = 25^{\circ}\text{C}$ unless otherwise specified, specified test circuit

Parameter	Symbol	Conditions	min	typ	max	Unit
Output voltage setting		$I_{IN} = 8\text{mA}$	40.0	40.5	41.0	V
Output voltage temperature coefficient		$T_c = 0$ to 105°C , $I_{IN} = 8\text{mA}$	-	7	-	mV/ $^{\circ}\text{C}$
[TR1]						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{mA}$, $V_{GS} = 0\text{V}$	900	-	-	V
Gate-source cutoff voltage	$V_{GS(off)}$	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	-	3.0	V
ON resistance	$R_{DS(on)}$	$I_D = 1.5\text{A}$, $V_{GS} = 10\text{V}$	-	5.0	7.0	Ω
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	500	-	pF
[ZD1]						
Zener voltage	V_Z	$I_Z = 5\text{mA}$	23.7	-	26.3	V

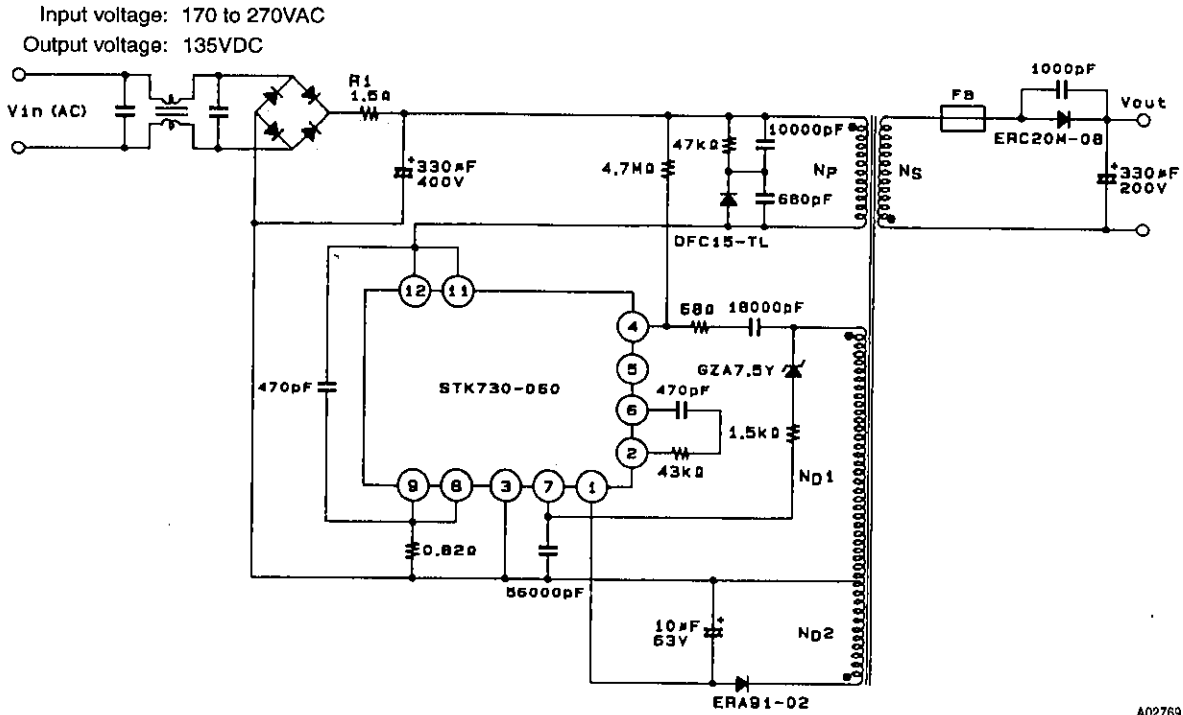
Circuit Function Diagram



A02766

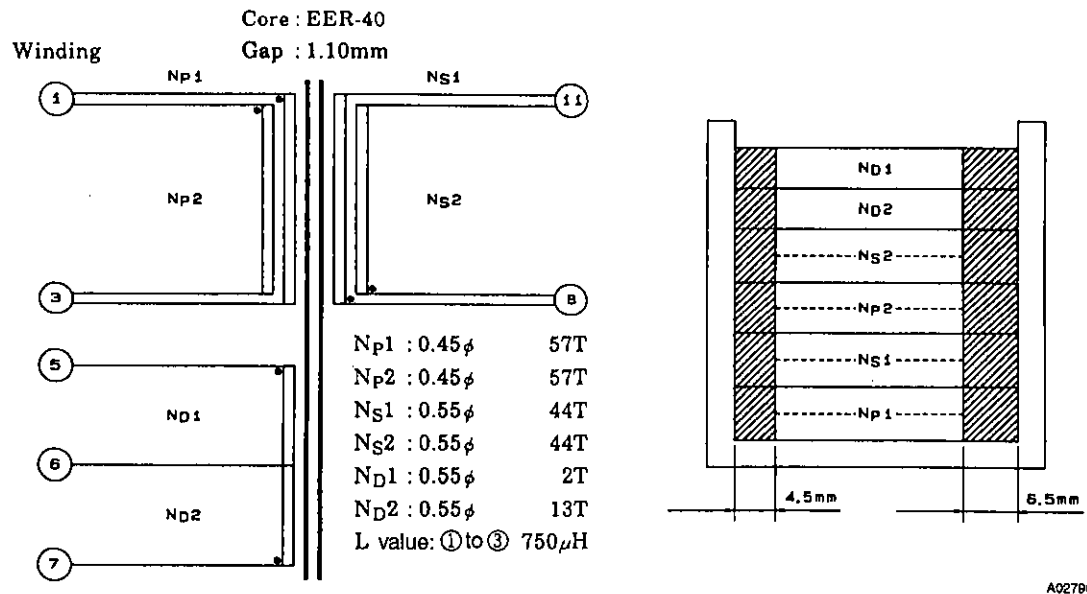


Sample Application Circuit (200V System)

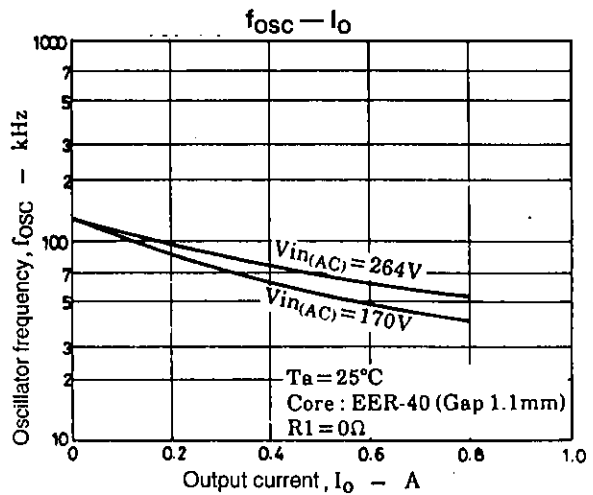
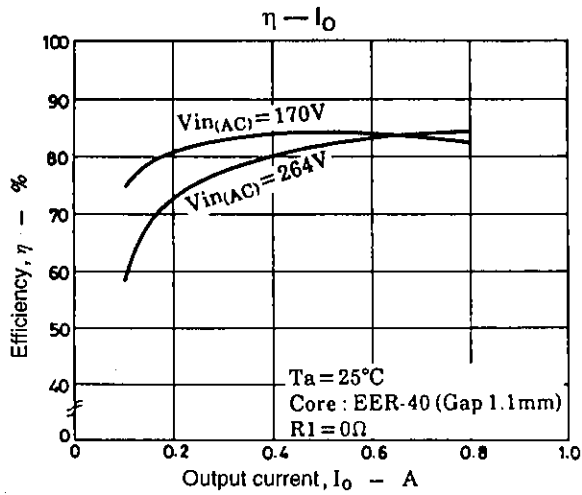
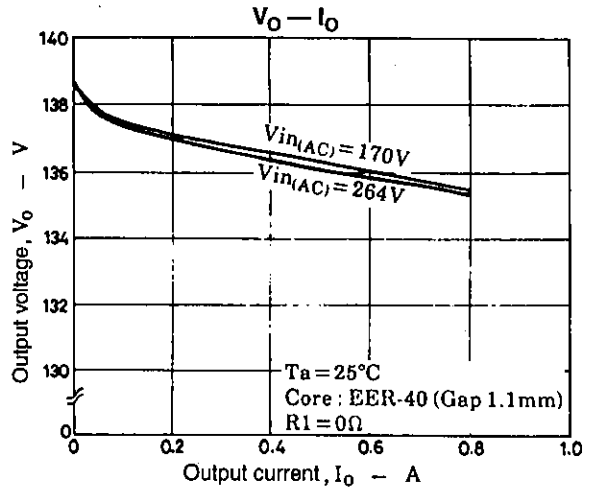
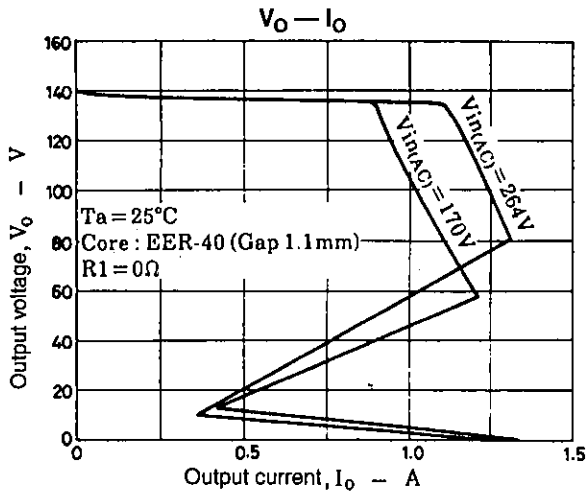


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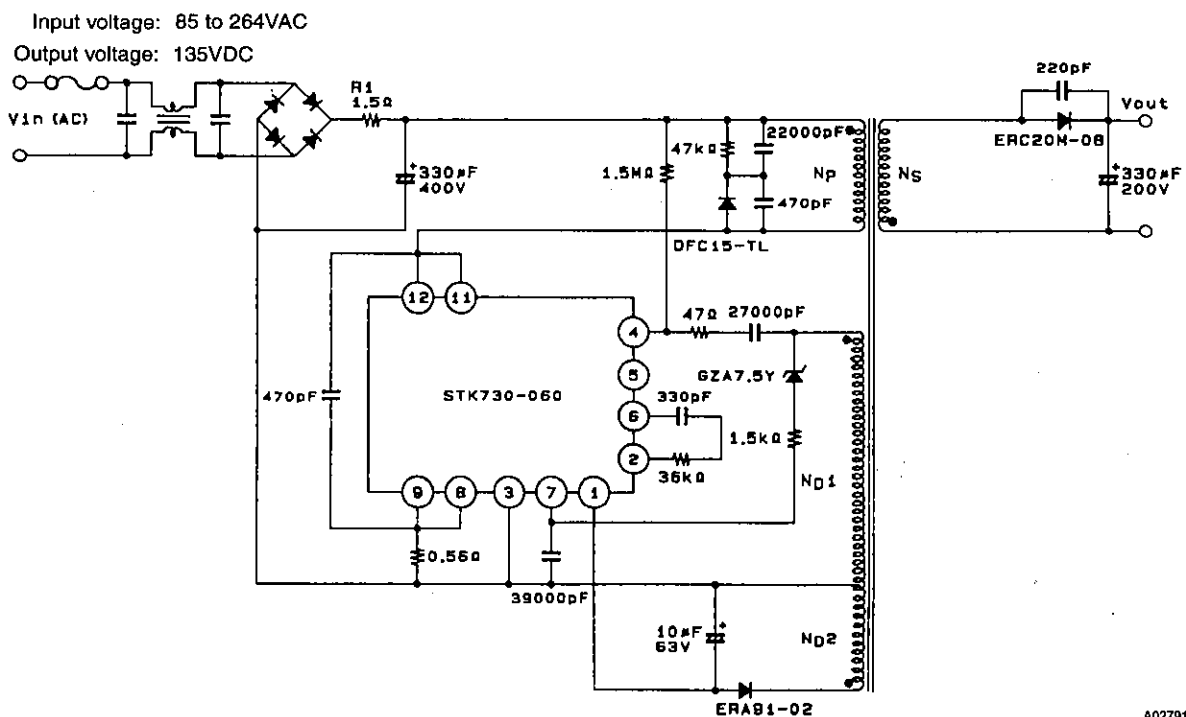
Pulse Transformer Specifications



A02780

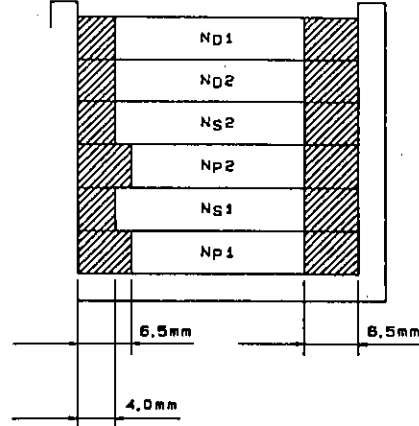
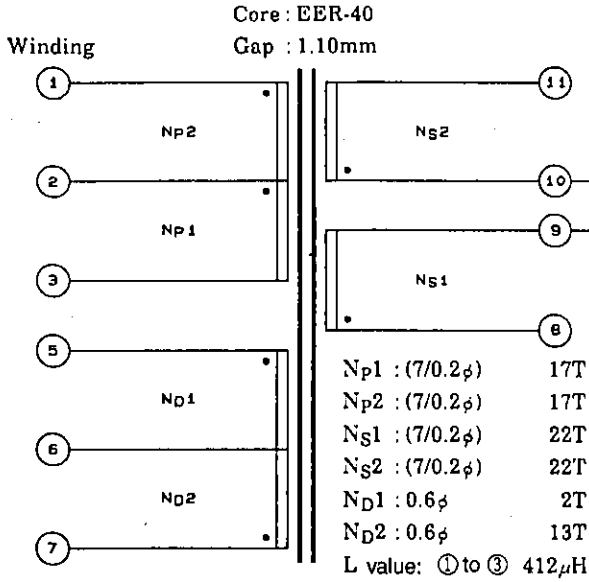


Sample Application Circuit (World Input System)

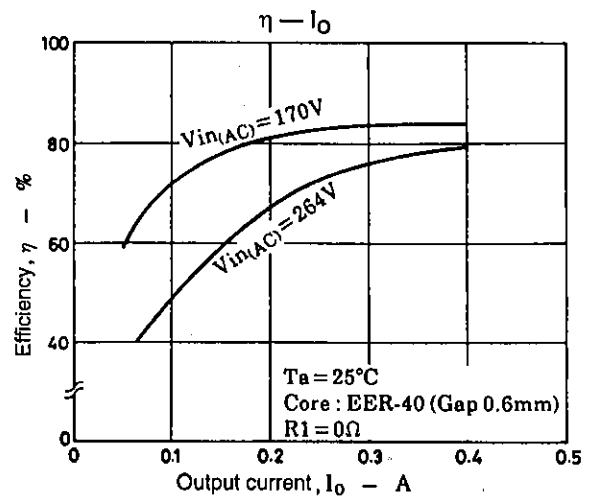
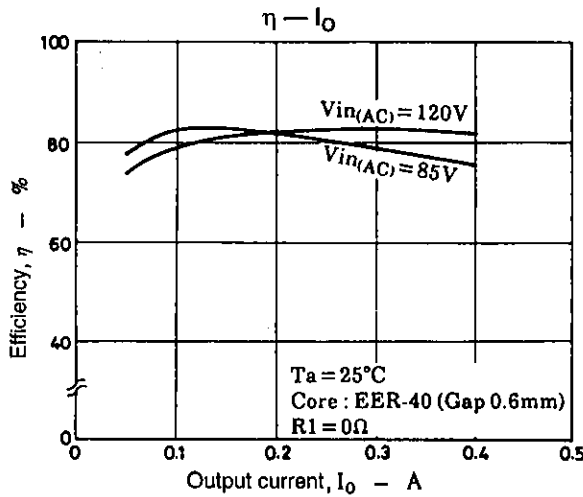
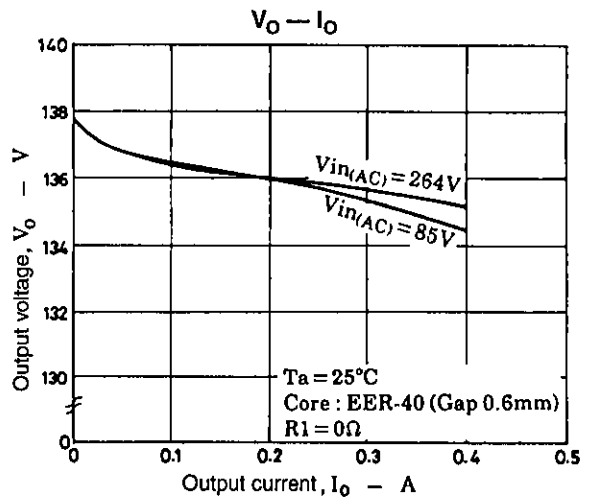
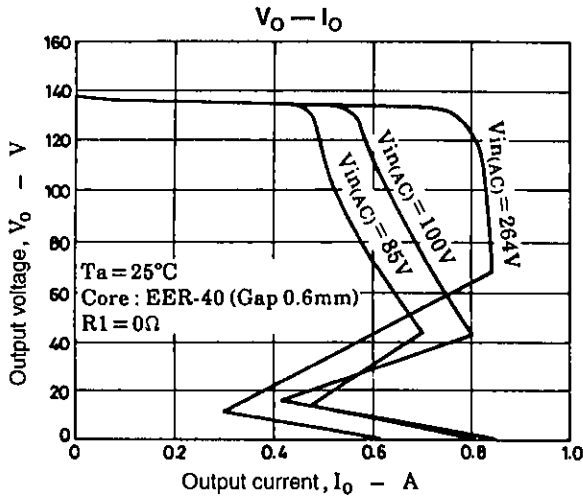


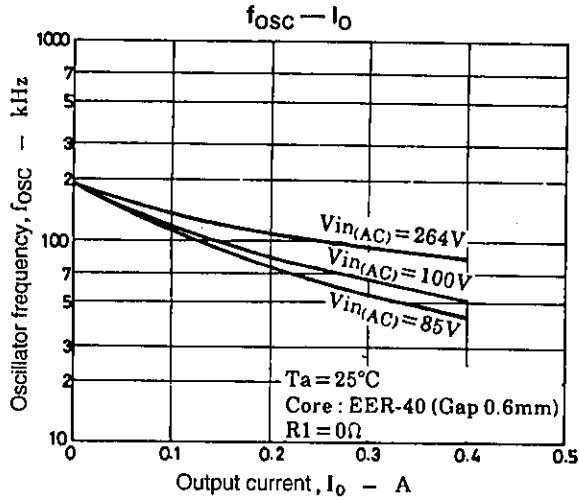
A02791

Pulse Transformer Specifications



A02792





Series Organization

These devices form a series with varying output power ratings.

Device	Maximum ratings				Operating characteristics			
	V _{DSS} [V]	T _{stg} [°C]	T _{c max} [°C]	T _{j max} [°C]	I _o [A]	Input voltage [V]	Output power [W]	ON resistance [Ω]
STK730-010	500	-30 to +115	+115	+150	6.0	85 to 132	110	1.4
STK730-020					8.0		145	0.8
STK730-030					10.0		180	0.7
STK730-040					12.0		210	0.55
STK730-050					15.0		280	0.3
STK730-060	900				3.0	170 to 264	110	5.0
STK730-070					5.0		180	3.0
STK730-080					6.0		210	2.0
STK730-090					8.0		280	1.2